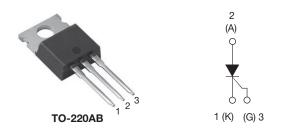
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Thyristor High Voltage, Phase Control SCR, 25 A



PRIMARY CHARACTERISTICS							
I _{T(AV)}	16 A						
V _{DRM} /V _{RRM}	1200 V						
V _{TM}	1.25 V						
I _{GT}	45 mA						
TJ	-40 °C to +125 °C						
Package	TO-220AB						
Circuit configuration	Single SCR						

FEATURES

- Easy control peak current at charger power up to reduce passive / electromechanical components
- Meets JESD 201 class 1A whisker test
- Flexible solution for reliable AC power **FREE** rectification
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- On-board and off-board EV/HEV battery chargers
- Renewable energy inverters

DESCRIPTION

The VS-25TTS12HM3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications.

OUTPUT CURRENT IN TYPICAL APPLICATIONS								
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS								
Capacitive input filter $T_A = 55$ °C, $T_J = 125$ °C, common heatsink of 1 °C/W	18	22	А					

MAJOR RATINGS AND CHARACTERISTICS									
PARAMETER	PARAMETER TEST CONDITIONS								
I _{T(AV)}	Sinusoidal waveform	16	А						
I _{RMS}		25	A						
V _{RRM} /V _{DRM}		1200	V						
I _{TSM}		320	А						
V _T	16 A, T _J = 25 °C	1.25	V						
dV/dt		500	V/µs						
dl/dt		150	A/µs						
TJ		-40 to +125	°C						

VOLTAGE RATINGS			
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} ∕I _{DRM} AT 125 °C mA
VS-25TTS12HM3	1200	1200	10

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 Document Number: 96530

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COMPLIANT

VS-25TTS12HM3



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ABSOLUTE MAXIMUM RATING	S							
PARAMETER	SYMBOL	TEST CO	NDITIONS	VAL	UES			
FANAMETEN	SYMBOL TEST CONDITIONS			TYP.	MAX.			
Maximum average on-state current	I _{T(AV)}	$T_{\rm C}$ = 93 °C, 180° conduc	tion half sine wave	1	6			
Maximum RMS on-state current	I _{RMS}			2	:5	А		
Maximum peak, one-cycle,		10 ms sine pulse, rated V	V _{RRM} applied	2	70			
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no vol	tage reapplied	3	20	1		
Maximum I ² t for fusing	l ² t	10 ms sine pulse, rated V	V _{RRM} applied	30	65	A ² s		
Maximum 1-t for fusing	1-1	10 ms sine pulse, no vol	tage reapplied	515		A-5		
Maximum I²√t for fusing	l²√t	t = 0.1 to 10 ms, no volta	t = 0.1 to 10 ms, no voltage reapplied			A²√s		
Maximum on-state voltage drop	V _{TM}	16 A, T _J = 25 °C		1.	25	V		
On-state slope resistance	r _t	T - 105 °C		12	2.0	mΩ		
Threshold voltage	V _{T(TO)}	$T_{\rm J} = 125 \ ^{\circ}{\rm C}$ 1.0			.0	V		
Maximum reverse and direct leakage		T _J = 25 °C	$\lambda = rotod \lambda = \Lambda $	0	.5			
current	I _{RM} /I _{DM}	T _J = 125 °C	$V_{R} = rated V_{RRM}/V_{DRM}$	1	0			
Holding current	Ι _Η	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 $^\circ C$		-	150	mA		
Maximum latching current	١L	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$			00			
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J max.$, linear to 80 °C, $V_{DRM} = R_g - k = open$			00	V/µs		
Maximum rate of rise of turned-on current	dl/dt			1:	A/µs			

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P _{GM}		8.0	w
Maximum average gate power	P _{G(AV)}		2.0	vv
Maximum peak positive gate current	+I _{GM}		1.5	A
Maximum peak negative gate voltage	-V _{GM}		10	V
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, $T_J = -10 \text{ °C}$	60	
	I _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \degree C$	45 mA	
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	20	
		Anode supply = 6 V, resistive load, $T_J = -10 \text{ °C}$	2.5	
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \degree C$	2.0	
voltage to trigger		Anode supply = 6 V, resistive load, $T_J = 125 \degree C$	1.0	V
Maximum DC gate voltage not to trigger	V _{GD}		0.25	
Maximum DC gate current not to trigger	I _{GD}	T _J = 125 °C, V _{DRM} = rated value	2.0	mA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9	
Typical reverse recovery time	t _{rr}	T₁ = 125 °C	4	μs
Typical turn-off time	tq	1j = 125 C	110	

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THERMAL AND MEC	THERMAL AND MECHANICAL SPECIFICATIONS								
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum junction and storage temperature range		T _J , T _{Stg}		-40 to 125	°C				
Maximum thermal resistance, junction to case		R _{thJC}	DC operation	1.1					
Maximum thermal resistance, junction to ambient		R _{thJA}		62	°C/W				
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.5					
Approximate weight				2	g				
Approximate weight				0.07	oz.				
Mounting torque	minimum			6 (5)	kgf ⋅ cm				
	maximum			12 (10)	(lbf ⋅ in)				
Marking device			Case style TO-220AB	25TT	S12H				

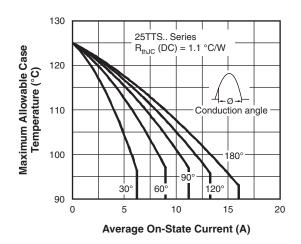


Fig. 1 - Current Rating Characteristics

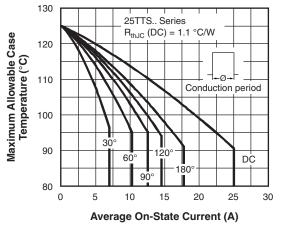


Fig. 2 - Current Rating Characteristics

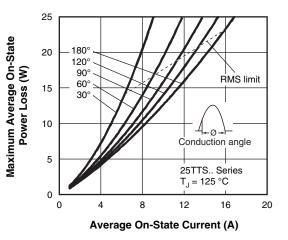


Fig. 3 - On-State Power Loss Characteristics

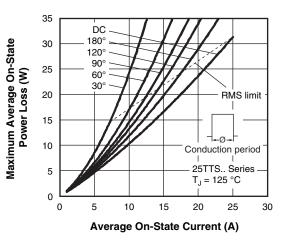


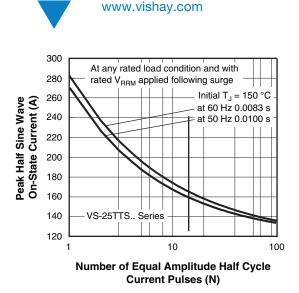
Fig. 4 - On-State Power Loss Characteristics

3

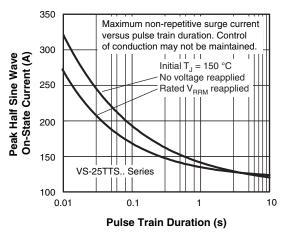
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VS-25TTS12HM3











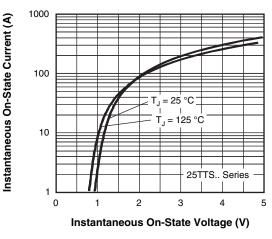


Fig. 7 - On-State Voltage Drop Characteristics

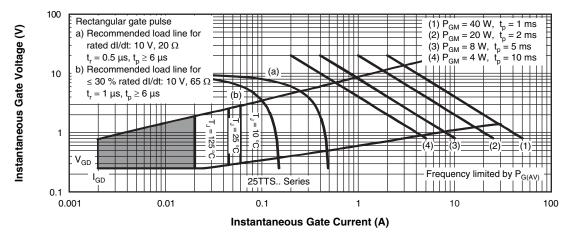


Fig. 8 - Gate Characteristics

VS-25TTS12HM3

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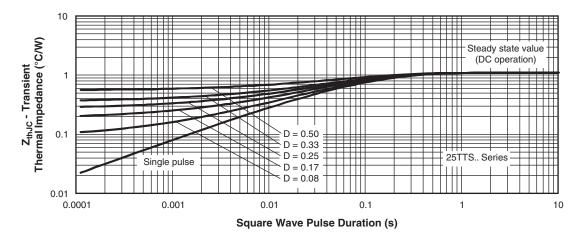
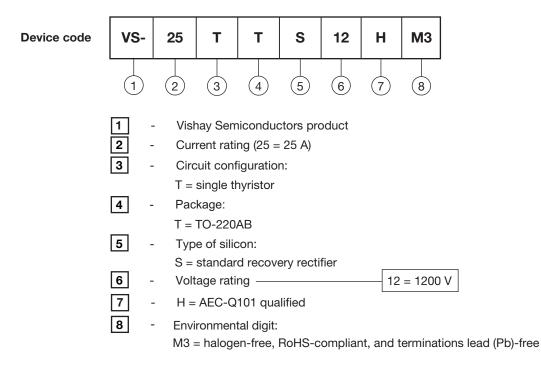


Fig. 9 - Thermal Impedance ZthJC Characteristics

ORDERING INFORMATION TABLE

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ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-25TTS12HM3	50	1000	Antistatic plastic tubes					

LINKS TO RELATED DOCUMENTS						
Dimensions www.vishay.com/doc?95222						
Part marking information	www.vishay.com/doc?95028					

Revision: 04-Jun-2018

Document Number: 96530

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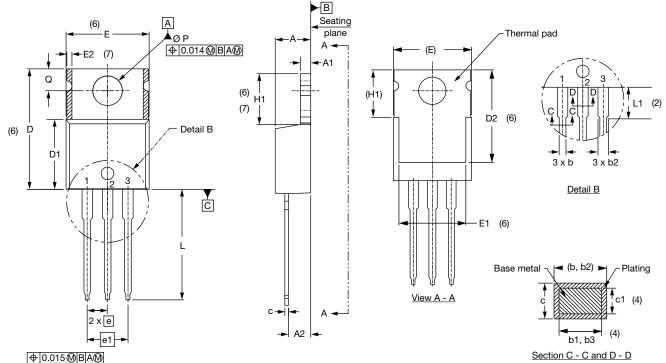
Outline Dimensions



Vishay Semiconductors

TO-220AB

DIMENSIONS in millimeters and inches



Lead tip

Conforms to JEDEC[®] outline TO-220AB

SYMBOL	MILLIMETERS		INCHES		NOTES	HES		SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES	123	STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES	
А	4.25	4.65	0.167	0.183			D2	11.68	12.88	0.460	0.507	6	
A1	1.14	1.40	0.045	0.055			Е	10.11	10.51	0.398	0.414	3, 6	
A2	2.56	2.92	0.101	0.115			E1	6.86	8.89	0.270	0.350	6	
b	0.69	1.01	0.027	0.040			E2	-	0.76	-	0.030	7	
b1	0.38	0.97	0.015	0.038	4		е	2.41	2.67	0.095	0.105		
b2	1.20	1.73	0.047	0.068			e1	4.88	5.28	0.192	0.208		
b3	1.14	1.73	0.045	0.068	4		H1	5.84	6.86	0.230	0.270	6, 7	
с	0.36	0.61	0.014	0.024			L	13.52	14.02	0.532	0.552		
c1	0.36	0.56	0.014	0.022	4		L1	3.32	3.82	0.131	0.150	2	
D	14.85	15.25	0.585	0.600	3		ØР	3.54	3.73	0.139	0.147		
D1	8.38	9.02	0.330	0.355			Q	2.60	3.00	0.102	0.118		

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Lead dimension and finish uncontrolled in L1

(3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

(4) Dimension b1, b3 and c1 apply to base metal only

⁽⁵⁾ Controlling dimensions: inches

⁽⁶⁾ Thermal pad contour optional within dimensions E, H1, D2 and E1

⁽⁷⁾ Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed

(8) Outline conforms to JEDEC[®] TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline

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